NSN 5961-01-059-3560

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-059-3560 **Inclosure Material:** Plastic **Overall Length:** Between 0.660 inches and 0.786 inches **Overall Height:** 0.300 inches **Overall Width:** 0.325 inches **Component Name And Quantity:** 4 transistor **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** 60.0 collector to base voltage, dc all transistor and 40.0 collector to emitter voltage/static/base open all transistor and 6.0 emitter to base voltage, dc all transistor **Current Rating Per Characteristic:** 50.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 4.2 watts small-signal input power, common-collector preset all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: npn **Terminal Type And Quantity:** 14 ribbon Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli